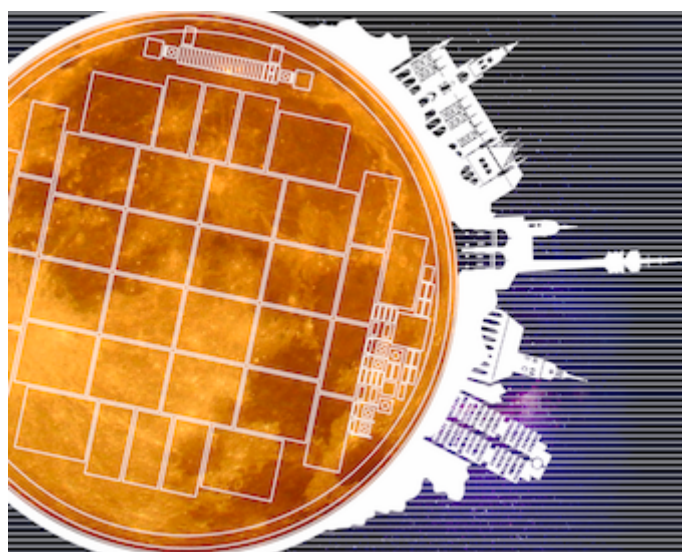


Session Program

19-21 Feb 2018



13th "Trento" Workshop on Advanced Silicon Radiation Detectors

Radiation Hardness

Max-Planck-Institut für Physik, Munich
Max-Planck-Institut für Physik (Werner-Heisenberg-Institut) Föhringer Ring 6 80805 München

Tuesday 20 February

17:00

Radiation Hardness: :

Session |

Location: Max-Planck-Institut für Physik, Munich, Max-Planck-Institut für Physik (Werner-Heisenberg-Institut)
Föhringer Ring 6 80805 München

17:00–17:15

Radiation hardness study of HV-CMOS sensors using Transient Current Technique**Speaker**

Armin Fehr

17:15–17:30

Characterization of acceptor removal in epitaxial silicon pad diodes**Speaker**

Pedro Dias De Almeida

17:30–17:45

edge-TCT results from AMS HV-CMOS test chips irradiated with 800 MeV protons**Speaker**

Daniel Muenstermann

18:05